WHAT IS CLAIMED IS:

1. A gallium nitride compound semiconductor light emission device comprising:

a substrate;

an n-type electrode region comprising an n-type transmissive electrode;

a gallium nitride compound semiconductor multilayer structure including an active layer; and

a p-type electrode region comprising a p-type transmissive electrode.

wherein the n-type transmissive electrode is of a type which is substantially transparent.

- 2. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the ptype transmissive electrode and the n-type transmissive electrode transmit light which is generated in the active layer and reflected from the substrate so that the light exits the light emission device.
- 3. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the n-type transmissive electrode is located outside of the p-type

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transmissive electrode.

4. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the n-type transmissive electrode is formed around a circumference of the p-type transmissive electrode.

5. A gallium nitride compound semiconductor light emission device according to claim 1,

wherein the gallium nitride compound semiconductor multilayer structure includes a buffer layer and an n-type gallium nitride compound semiconductor layer, and

wherein the n-type transmissive electrode is formed on a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor layer in a region neighboring the buffer layer.

6. A gallium nitride compound semiconductor light emission device according to claim 1.

wherein the n-type electrode region further comprises an n-type pad electrode, and

wherein the p-type electrode region further comprises a p-type pad electrode.

7. A gallium nitride compound semiconductor light emission device according to claim 6, wherein the n-type pad electrode and the p-type pad electrode are provided substantially along one side of a light emitting face of the gallium nitride compound semiconductor light emission device.

- 8. A gallium nitride compound semiconductor light emission device according to claim 6, wherein the p-type pad electrode is formed in the vicinity of a center of a light emitting face of the gallium nitride compound semiconductor light emission device.
- 9. A gallium nitride compound semiconductor light emission device according to claim 1, wherein the n-type transmissive electrode comprises at least one of a thin metal film and an oxide semiconductor.
- 10. A gallium nitride compound semiconductor light emission device according to claim 6, wherein the n-type pad electrode is of a type which realizes a Schottky contact.

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11. A gallium nitride compound semiconductor light emission device according to claim 6, wherein the n-type pad electrode comprises at least one material selected from the group consisting of:

Pd/Au, Ni/Au, Pt/Au, Pd/Ni/Au, Pd/Al, Ni/Al, Pt/Al, Pd/Ni/Al, Pd/oxide semiconductor, Ni/oxide semiconductor, Pt/oxide semiconductor, and Pd/Ni/oxide semiconductor;

or an alloy comprising one or more materials selected from the above group.

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